# MicroCapacitance (MC) SIDACtor Device



The TO-92 MC *SIDACtor* series is intended for applications sensitive to load values. Typically, high speed connections require a lower capacitance.  $C_{\rm O}$  values for MC devices are 40% lower than a standard EC part.

This MC *SIDACtor* series is used to enable equipment to meet various regulatory requirements including GR 1089, ITU K.20, K.21, and K.45, IEC 60950, UL 60950, and TIA-968-A (formerly known as FCC Part 68) without the need of series resistors.

#### **Electrical Parameters**

Part Number *	V <sub>DRM</sub> Volts	V <sub>S</sub> Volts	V <sub>T</sub> Volts	I <sub>DRM</sub> μAmps	I <sub>S</sub> mAmps	I <sub>T</sub> Amps	I <sub>H</sub> mAmps	C <sub>O</sub> pF
P0640EC MC	58	77	4	5	800	2.2	150	60
P1500EC MC	140	180	4	5	800	2.2	150	50
P2600EC MC	220	300	4	5	800	2.2	150	40
P3100EC MC	275	350	4	5	800	2.2	150	40

<sup>\*</sup> For surge ratings, see table below.

### General Notes:

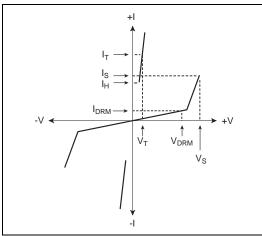
- All measurements are made at an ambient temperature of 25 °C. IPP applies to -40 °C through +85 °C temperature range.
- IPP is a repetitive surge rating and is guaranteed for the life of the product.
- · Listed SIDACtor devices are bi-directional. All electrical parameters and surge ratings apply to forward and reverse polarities.
- V<sub>DRM</sub> is measured at I<sub>DRM</sub>.
- V<sub>S</sub> is measured at 100 V/μs.
- Special voltage ( $V_S$  and  $V_{DRM}$ ) and holding current ( $I_H$ ) requirements are available upon request.
- Off-state capacitance ( $C_{\text{O}}$ ) is measured at 1 MHz with a 2 V bias.

## **Surge Ratings**

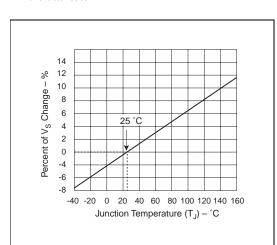
Series	l <sub>PP</sub> 2x10 μs Amps	I <sub>PP</sub> 8x20 μs Amps	I <sub>PP</sub> 10x160 μs Amps	I <sub>PP</sub> 10x560 μs Amps	I <sub>PP</sub> 10x1000 μs Amps	I <sub>TSM</sub> 60 Hz Amps	di/dt Amps/µs
С	500	400	200	150	100	50	500

### **Thermal Considerations**

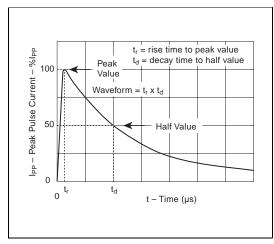
Package	Symbol	Parameter	Value	Unit
	TJ	Operating Junction Temperature Range	-40 to +150	°C
TO-92	Ts	Storage Temperature Range	-65 to +150	°C
	$R_{ hetaJA}$	Thermal Resistance: Junction to Ambient	90	°C/W



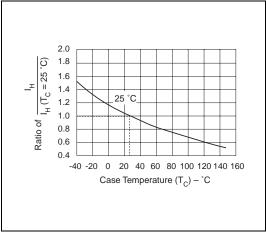
V-I Characteristics



Normalized V<sub>S</sub> Change versus Junction Temperature



 $t_{r} \ x \ t_{d}$  Pulse Wave-form



Normalized DC Holding Current versus Case Temperature